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# Magnetic and transport properties in the field-induced phase transitions in Ni50Mn50-xInx Heusler alloys

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# Introduction

# The search for ferromagnetic materials suitable for application in semiconductor spintronics devices.

To allow efficient spin injection into the semiconductor, these materials must satisfy at least the following

- 1) Curie temperature significantly higher than the room temperature, the working temperature of semiconductors used industrially.
- 2) A very high spin polarization of the electron states at the Fermi level.

#### Heusler alloys were predicted to be Half-metals

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#### PHYSICAL REVIEW LETTERS

20 JUNE 1983

#### New Class of Materials: Half-Metallic Ferromagnets

R. A. de Groot and F. M. Mueller

Research Institute for Materials, Faculty of Science, Toernooiveld, 6525 ED Nijmegen, The Netherlands

and

P. G. van Engen and K. H. J. Buschow Philips Research Laboratories, 5600 JA Eindhoven, The Netherlands

(Received 21 March 1983)

The band structure of Mn-based Heusler alloys of the  $C1_b$  crystal structure (MgAgAs type) has been calculated with the augmented-spherical-wave method. Some of these magnetic compounds show unusual electronic properties. The majority-spin electrons are metallic, whereas the minority-spin electrons are semiconducting.

PACS numbers: 71.10.+x, 71.25.Pi, 75.20.En

Magnetic materials based on the  $L2_1$  and  $C1_b$ crystallographic phases have been of interest to both theorists and experimentalists since they were first considered by Heusler.<sup>1</sup> His interest focused on the unusual result that some of these materials in these crystallographic phases were

ture types can be described by means of four interpenetrating fcc lattices. For the ordinary  $L2_1$ Heusler alloys these fcc lattices can be characterized by the positions  $X_1 \left(\frac{1}{4}\frac{1}{4}\frac{1}{4}\right)$ ,  $X_2 \left(\frac{3}{4}\frac{3}{4}\frac{3}{4}\right)$ , Y(000), and  $Z \left(\frac{1}{2}\frac{1}{2}\frac{1}{2}\right)$ . The same holds for the  $C1_b$ structure with the exception that the  $X_1$  positions

## Half metal key material candidate for spintronics

$$polarization = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}} = 100\%$$

 $n_{\uparrow}$  and  $n_{\downarrow}$  are electron density

 $n_{\uparrow}$  Or  $n_{\downarrow}$  =0

## Nonmagnetic vs. Magnetic Materials



## Half metals



Spins of all the conducting electrons pint to the same direction "Up"

## Heusler alloys of Higher-spin-polarization (much higher than the conventional ferromagnetic metals)

- spin polarization of the Co<sub>2</sub>MnSi Heusler compound has been estimated to be 61% at 10 K. (Kammerer et al. APL85, 79,(2004))
- Point-contact Andreev reflection measurements of the spin polarization yield polarization values for Co<sub>2</sub>MnSi and NiMnSb of 56% and 45%, respectively

(L. Ritchie et al., Phys. Rev. 68, 104430(2003)).

# Polarization of Ferromagnetic materials

Material studied	Point	Base	N	P <sub>T</sub> (%)	P <sub>c</sub> (%)
NiFe	Nb	Ni <sub>o s</sub> Fe <sub>o 2</sub> film	14	25 ± 2	37 ± 5
Co	Nb	Co foil	7	35 ± 3	42 ± 2
Fe	Та	Fe film	12	40 ± 2	45 ± 2
	Fe	Ta foil	14		46 ± 2
	Nb	Fe film	4		42 ± 2
	Fe	V crystal	10		45 ± 2
Ni	Nb	Ni foil	4	23 ± 3	$46.5 \pm 1$
	Nb	Ni film	5		43 ± 2
	Ta	Ni film	8		$44 \pm 4$
NiMnSb	Nb	NiMnSb film	9	_	58 ± 2.3
LSMO	Nb	La <sub>o.7</sub> Sr <sub>o.3</sub> MnO <sub>3</sub> film	14	_	78 ± 4.0
CrO <sub>2</sub>	Nb	CrO <sub>2</sub> film	9	_	90 ± 3.6

# Ferromagnetic shape memory alloys

- Ferromagnetic Heusler alloys are well known ferromagnetic shape memory alloys
  - Martensitic transformation
  - Magnetic field induced strain
  - Applications in actuators

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## Typical Heusler alloys -Ni<sub>2</sub>MnGa



## **Characteristics**

#### Thermal-elastic martensitic transformation Shape memory effect



Spontaneous shape memory effect in single crystals



# **Mechanism of field induced strain**



H≥H<sub>A</sub>

# **Characteristics of Ni2MnGa**

- High temperature phase (or austenite) : ferromagnetic, low magnetic anisotropy cubic lattice
- Low temperature phase (martensite): ferromagnetic, strong magnetic anisotropy, tetragonal lattice
- Both phase are ferromagnetic metals

#### M(T) curves with different applied magnetic fields F. Zuo et al PRB58,11127(1998)



#### **Temperature-dependent resistivity** Zuo et al, J. Phys.: Condens. Matter **11** (1999) 2821–2830.)



# CoNiGa alloys



#### **Magnetoresistance**



### Ni<sub>2</sub>MnColn crystals

Nature 439, 957(2006)



 $E = -\vec{B} \bullet \vec{M}$ 

# Ni<sub>50</sub>Mn<sub>50-x</sub>In<sub>x</sub> single crystals (x=14-16.3)

- single crystals were grown at a rate of 5–30 mm/h using a Czochralski instrument with a cold crucible system
- X-ray: High temperature phase is L21-type ordered structure with a lattice constant a=6.006Å.
- Cooling to 93K, the crystal structure changes to an orthorhombic structure with a rather complex martensitic modulated sub-structure.

# Magnetic, electrical and thermal transport measurements

- Magnetic measurements: Quantum Design SQUID magnetometer, 2-400 K, 5 Tesla
- Transport measurements: Quantum Design Physical Property Measurement system (PPMS), 2-400 K, 9Tesls
- Specific Heat: PPMS

## M(T) and $\rho(T)$ in different fields

#### (APL91,2007)

#### **Features:**

- (1) The martensitic transformation with thermal hysteresis.
- (2) Martensitic transformation is magnetic field dependent.
- (3) Magnetic field shift transition to lower temperature.
- (4) The transformation can be totally suppressed by magnetic field.
- (5) Currie temperature Tc=315K
- (6) Low-T martensite is ferrimagnetic, poor metal.
- (7) High T, ferromagnetic austenite, metal
- (8) Martensitic transformation is accompanied by a metal-poor metal transition.

#### **GMR** in a broad temperature range



### **GMR** in a broad temperature range



At 5K, for Crystal 1 MR =86%

## Giant MR and Tunneling MR

Giant MR (GMR)  $\rho_T = \rho_{\parallel}$ 



# M(H) and MR(H) in different fields

#### M(H) curves indicate a metamagnetic behavior or field-induced phase transition

# ρ(H) or MR (H) has the similar transition fields



# Superzone Gap

#### Superzone gap:

- The antiferromagnetic lattice does not commensurate with the crystal lattice, which leads to a new Brillouin boundary
- (a gap appearing on the Fermi surface).
- In intermetallic alloys, the large MR results from the collapsing of the "superzone gap" due to field induced first order phase transition.

(UNiGa, PRL77,5253).

## Ni<sub>50</sub>Mn<sub>33.7</sub>In<sub>16.3</sub> single crystal

Showing the similar martensitic transformation, metal-poor metal transition, GMR and Giant Thermal conductivity.

Free electron Wiedemann-Franz law

$$\frac{k}{\sigma T} = L = 2.45 \times 10^{-8} W \Omega K^{-2}$$

the upper bound for  $\Delta \kappa_{el}$ 

The sum of  $\Delta \kappa_{\text{el}}$  and zero-field  $\kappa$  gives total  $\kappa$ 



#### M(H) and MTC(H) in different fields





At 5K, for Crystal 1 MR =86%

# **Specific heat measurement**



# **Specific heat measurement**



# MR obtained from Specific Heat measurement



 $MR = [\rho(0) - \rho(9T)] / \rho(0) = [1 / n_0 - 1 / n_{9T}] . n_0$ 

#### **MR =86.4%**

**Excellent** agreement

# Conclusion

Large magnetoresistance (MR) and magnetothermal conductivity are due to the collapse of Superzone gap, when the magnetic field induced ferrimagnetic to the ferromagnetic phase transformation happens

# A combined giant inverse and normal magnetocaloric effect for room-temperature magnetic cooling (PRB76,2007)

# Magnetocaloric effect (MCE)



$$\Delta S_M = S_M(H_2,T) - S_M(H_1,T) = \int_{H_1}^{H_2} \left(\frac{\partial M(H,T)}{\partial T}\right)_H dH$$



**Temperature (K)** 

**Only near the T<sub>C</sub>, dM/dT is large, leads to a significant MCE Room temperature application: GdGeSi , LAFeSi alloys** 

## Ni<sub>50</sub>Mn<sub>33.13</sub>In<sub>13.90</sub> single crystal



#### Metamagnetism vs Phase-transition



# Calculation of entropy change

$$-\Delta S_{M} = \sum_{i} \frac{1}{T_{i+1} - T_{i}} (M_{i} - M_{i+1}) \Delta H_{i}$$

$$\frac{\Delta\theta}{\Delta H} = \frac{\Delta M}{\Delta S} = consant$$

**Clausius-Clapeyron equation** 

# Entropy change vs temperature





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